

L Number	Hits	Search Text	DB	Time stamp
1	29	(nb or niobium) near2 monoxide	USPAT; US-PGPUB; JPO	2004/09/20 10:46
2	80551	gate adj (dielectric or insulat\$3 or oxide)	USPAT; US-PGPUB; JPO	2004/09/20 10:42
3	611220	gate\$1	USPAT; US-PGPUB; JPO	2004/09/20 10:42
4	1130294	pattern\$3	USPAT; US-PGPUB; JPO	2004/09/20 10:43
5	456653	transistor\$1	USPAT; US-PGPUB; JPO	2004/09/20 10:44
6	0	((nb or niobium) near2 monoxide) with gate\$1) and (gate adj (dielectric or insulat\$3 or oxide)) and transistor\$1 and pattern\$3	USPAT; US-PGPUB; JPO	2004/09/20 10:44
7	61272	(gate adj (dielectric or insulat\$3 or oxide)) and transistor\$1	USPAT; US-PGPUB; JPO	2004/09/20 10:45
8	0	((nb or niobium) near2 monoxide) same gate\$1	USPAT; US-PGPUB; JPO	2004/09/20 10:45
9	0	((gate adj (dielectric or insulat\$3 or oxide)) and transistor\$1) and ((nb or niobium) near2 monoxide) same gate\$1)	USPAT; US-PGPUB; JPO	2004/09/20 10:45
10	1	((nb or niobium) near2 monoxide) and gate\$1	USPAT; US-PGPUB; JPO	2004/09/20 10:45
11	520	((nb or niobium) near2 monoxide) or nbo	USPAT; US-PGPUB; JPO	2004/09/20 10:47
12	20	((nb or niobium) near2 monoxide) or nbo) and (gate adj (dielectric or insulat\$3 or oxide)) and gate\$1 and transistor\$1	USPAT; US-PGPUB; JPO	2004/09/20 10:47